

B⁹ cont'd
exposing said metal film to a second gas atmosphere at an elevated substrate temperature.

4. (Amended) A method as claimed in claim 1, wherein said second gas atmosphere includes hydrogen and/or nitrogen.

B¹⁰
5. (Amended) A method as claimed in claim 1, wherein said step of exposing said metal film to said second gas atmosphere is conducted at a temperature of 250-500°C.

B¹¹
11. (Amended) A method as claimed in claim 8, further comprising, after said step of forming said metal film, a thermal annealing process applied to said metal film.

See the attached Appendix for the changes made to effect the above claim(s)

IN THE ABSTRACT OF THE DISCLOSURE:

Please delete the present Abstract of the Disclosure and replace it with the following new Abstract of the Disclosure.

B¹²
A method for fabricating a semiconductor device includes the steps of forming a barrier conductor layer on a substrate, exposing the barrier conductor layer to a first reducing gas atmosphere at an elevated substrate temperature, forming a metal film on the barrier conductor layer by a CVD process, and exposing the metal film to a second gas atmosphere at an elevated substrate temperature.

See the attached Appendix for the changes made to effect the above Abstract.

IN THE ABSTRACT OF THE DISCLOSURE:

The abstract is changed as follows:

A method for fabricating a semiconductor device includes the steps of forming a barrier conductor layer on a substrate, exposing the barrier conductor layer to a first reducing gas atmosphere at an elevated substrate temperature, forming a metal film on the barrier conductor layer by a CVD process, and exposing the metal film to a second [reducing] gas atmosphere at an elevated substrate temperature.

End of Appendix